



Next-Generation Power Electronics Technology with Vehicle Electrification

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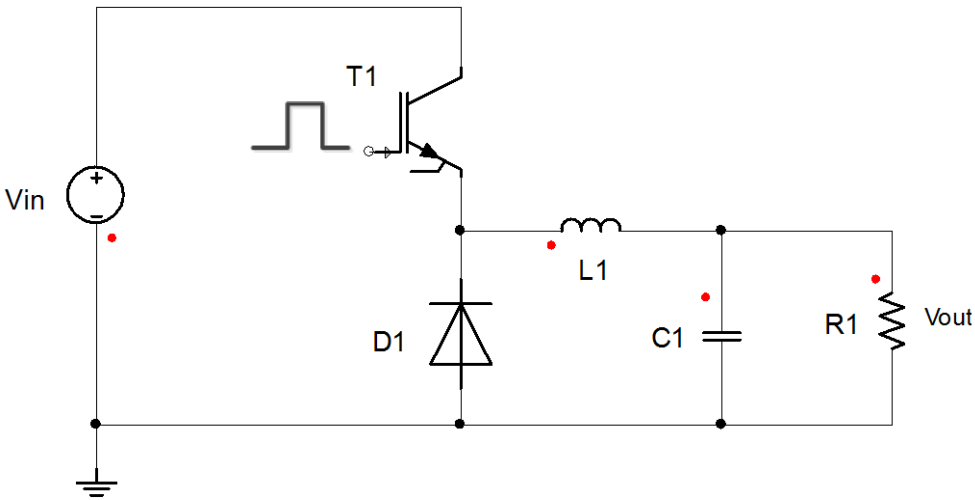
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Agenda

- **WBG Semiconductors vs Silicon Devices;**
- **WBG Semiconductors: Challenges and Opportunities;**
- **WBG Semiconductors in EVs;**
- **Conclusions.**

Challenges of Power Electronics

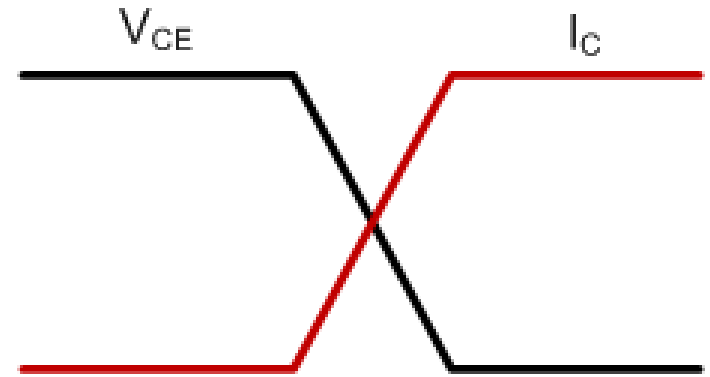


$$V_o = DV_{in}$$

$$L = \frac{V_o}{\Delta I_L f_s} (1 - D)$$

$$C = \frac{V_o}{8L\Delta V_o f_s^2} (1 - D)$$

**The higher f_s
the merrier.**



$$P_{swon} = \frac{V_{CE} I_C \Delta t}{6} f_s$$

**The lower f_s
the merrier.**

15 Years ago...

We believed...

- 1. ~10kHz is the best switching frequency for IGBTs;**
- 2. MOSFET is good for <1kW application;**
- 3. MV (>1000V) drive should use ~1kHz;**
- 4. Wide-bandgap devices are far away.**

Mega-Watt Motor Drive System

An IGCT based Three-level Inverter was built to drive a 6000V/1.25MW Induction Motor.



4000V/4500A IGCT



6000V/1.25MW IGCT based Three-Level NPC Inverter

Mega-Watt Motor Drive System

An IGCT based Three-level Inverter was built to drive a 6000V/1.25MW Induction Motor.



6000V/1.25MW System



6000V/1.25MW Motors



1.25MW Waste Water Pumps



Waste-Water Tank

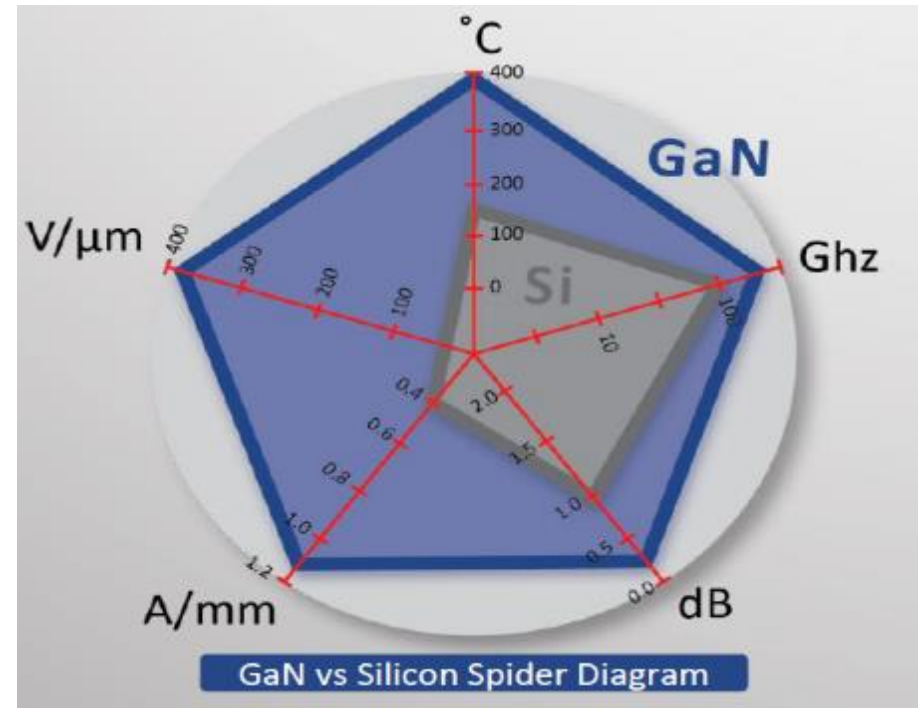
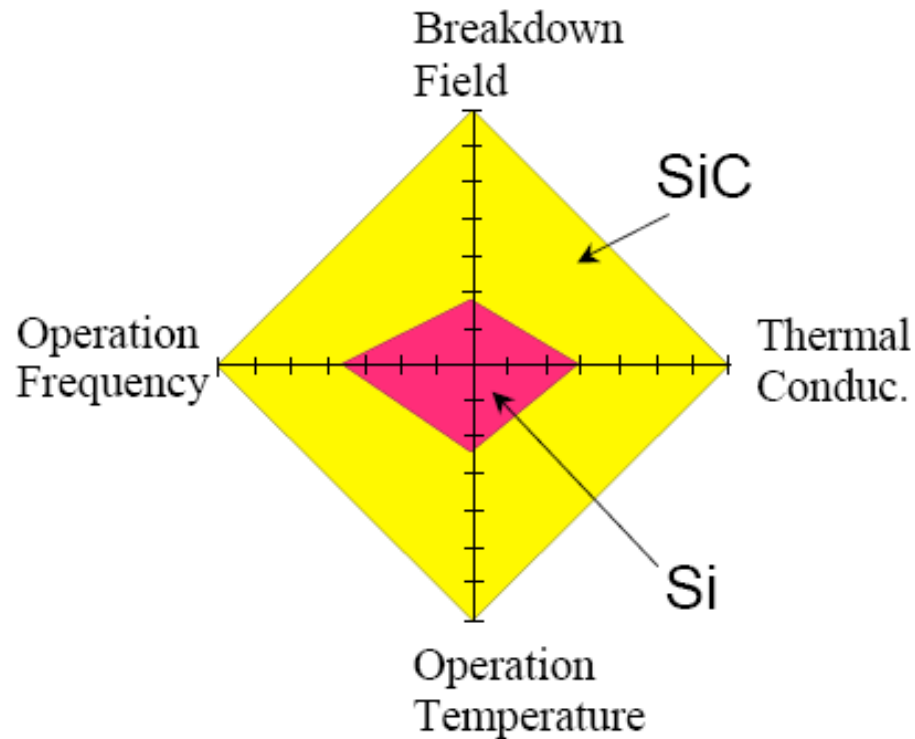
5 Years ago...

We witnessed...

- 1. Fast-speed IGBTs ($f_s > 50\text{kHz}$) are on the market;**
- 2. Cool MOSFETs can easily reach $>10\text{kW}$;**
- 3. SiC devices enables higher f_s for MV motor drive systems;**
- 4. GaN are on the agenda.**

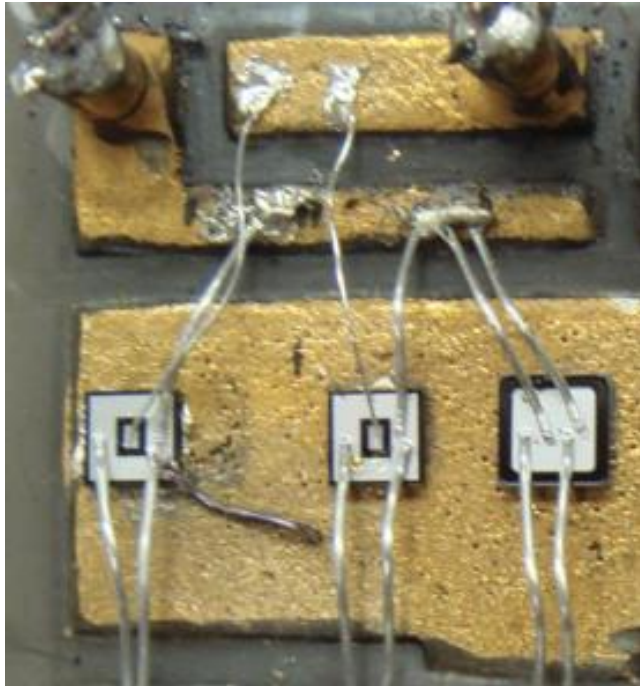
SiC and GaN

Wide bandgap indicates higher thermal capability, which means **less heatsink or higher switching frequency.**

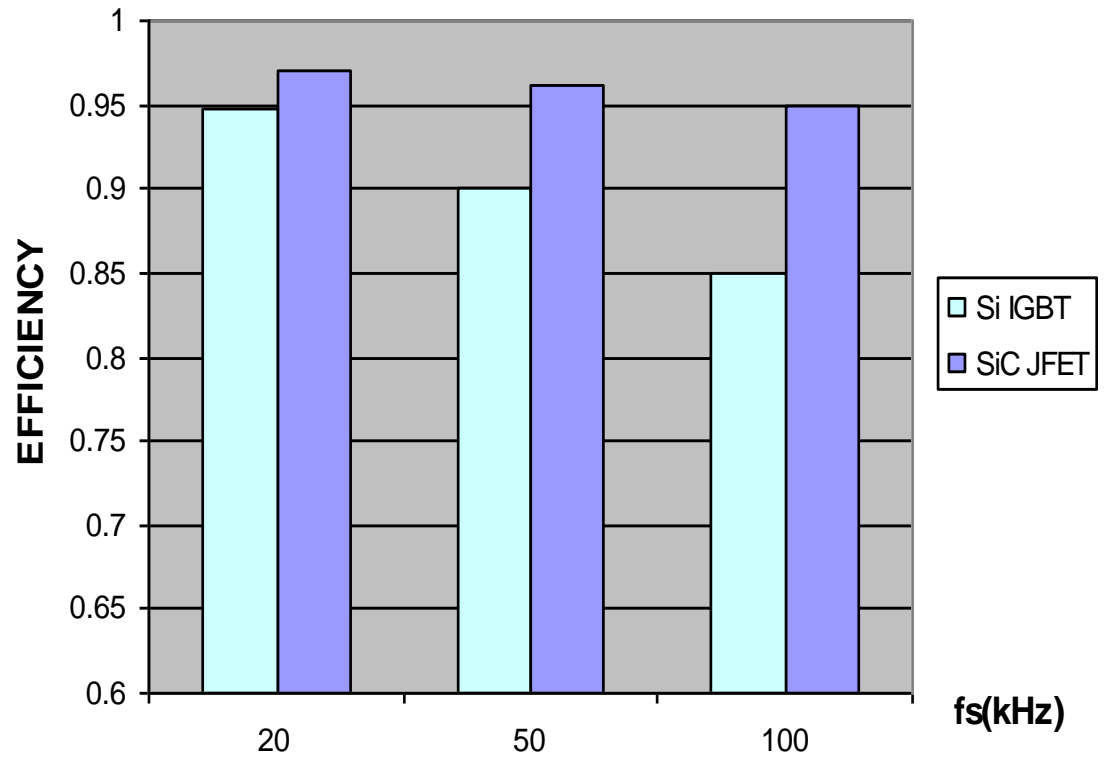


	Si	SiC	GaN
Bandgap	1.1eV	3.3eV	3.4eV
Dielectric	0.3MV/cm	2.5~3MV/cm	3MV/cm

SiC JFETs



SiC JEFET Die



Efficiency

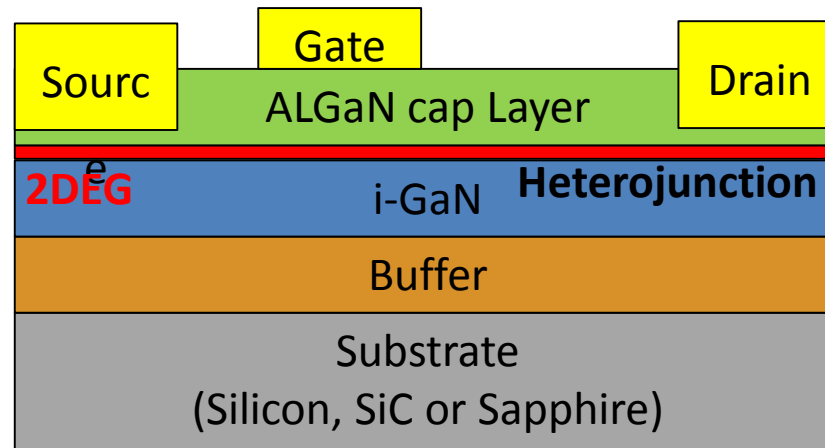
Today...

We witnessed

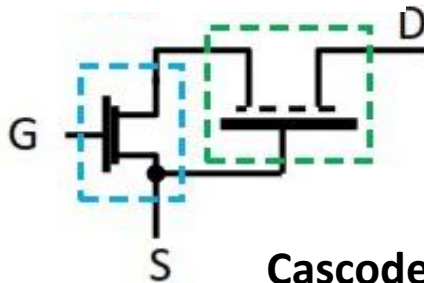
- 1. Silicon devices keep enhancing their performance;**
- 2. SiC MOSFET focuses on >1200V market;**
- 3. GaN devices emerge in <650V applications;**
- 4. Wide-bandgap devices are believed as the future.**

GaN Devices

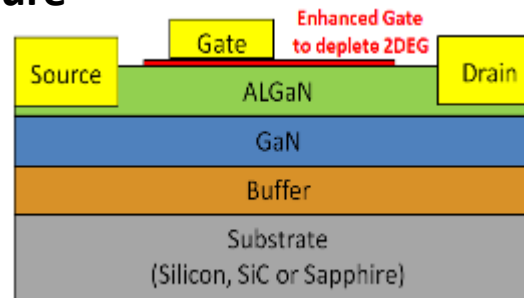
normally
on



normally
off



Cascode Structure



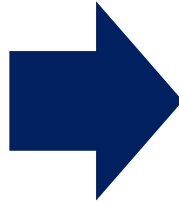
Enhanced Mode GaN



GaN Devices

Material Property

- High electron mobility
- Wide band gap
- High breakdown field
- High electron velocity



Electrical Performance of E-mode HEMTs

Reverse Conduction

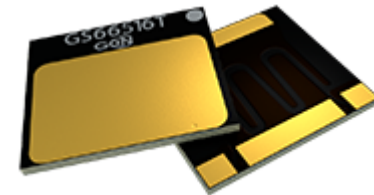
- No reverse recovery

$$V_{sd} = V_{sg} + V_{th_gd} + R_{dson} * I_{ds}$$

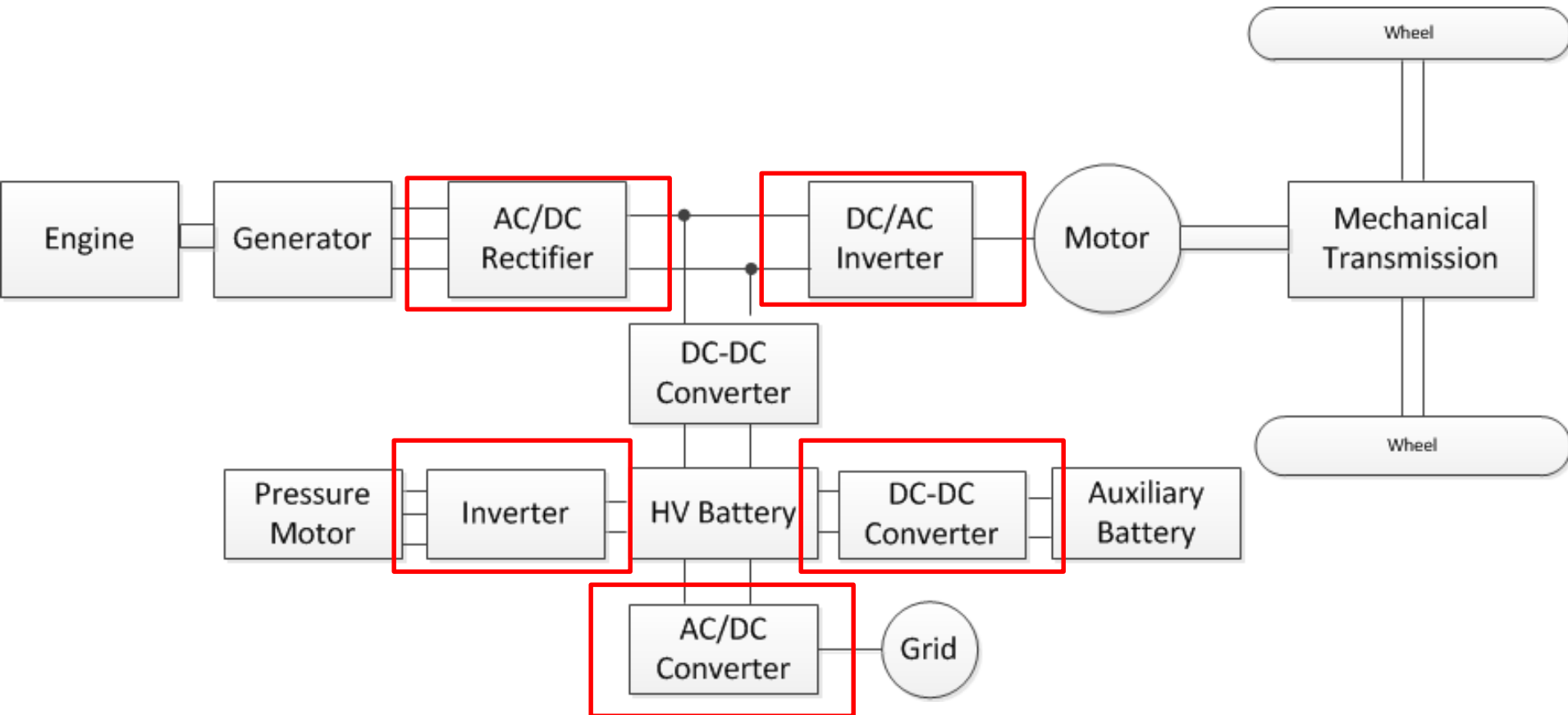
2DEG

- Low R_{dson}
- Dynamic R_{dson}

- Fragile gate
- Low Threshold Voltage
- low Capacitance
- High transition speed
- Low Switching loss
- High di/dt

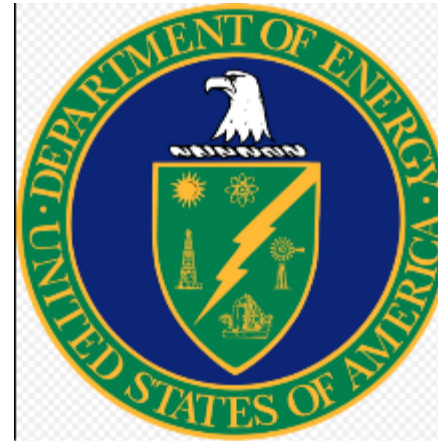


WBG devices in PHEV



1. SiC Based Dual Inverters for E-Truck

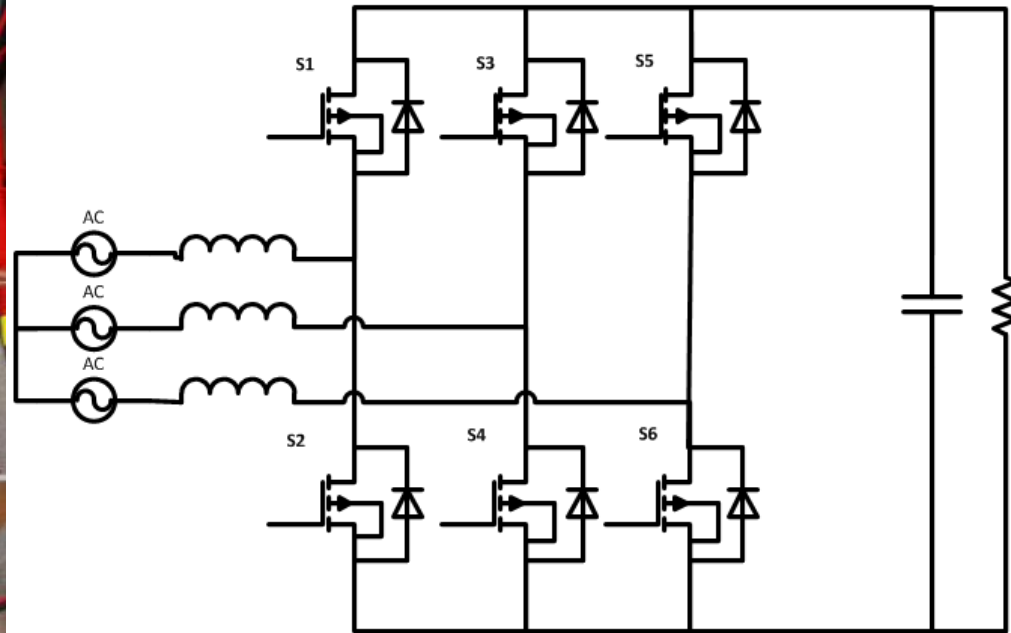
- 120kW dual inverter;
- All SiC devices;
- All Hard switching;
- Bidirectional power for V2G and G2V;
- >3.3kW/L.



2. Magna 11kW Battery Chargers



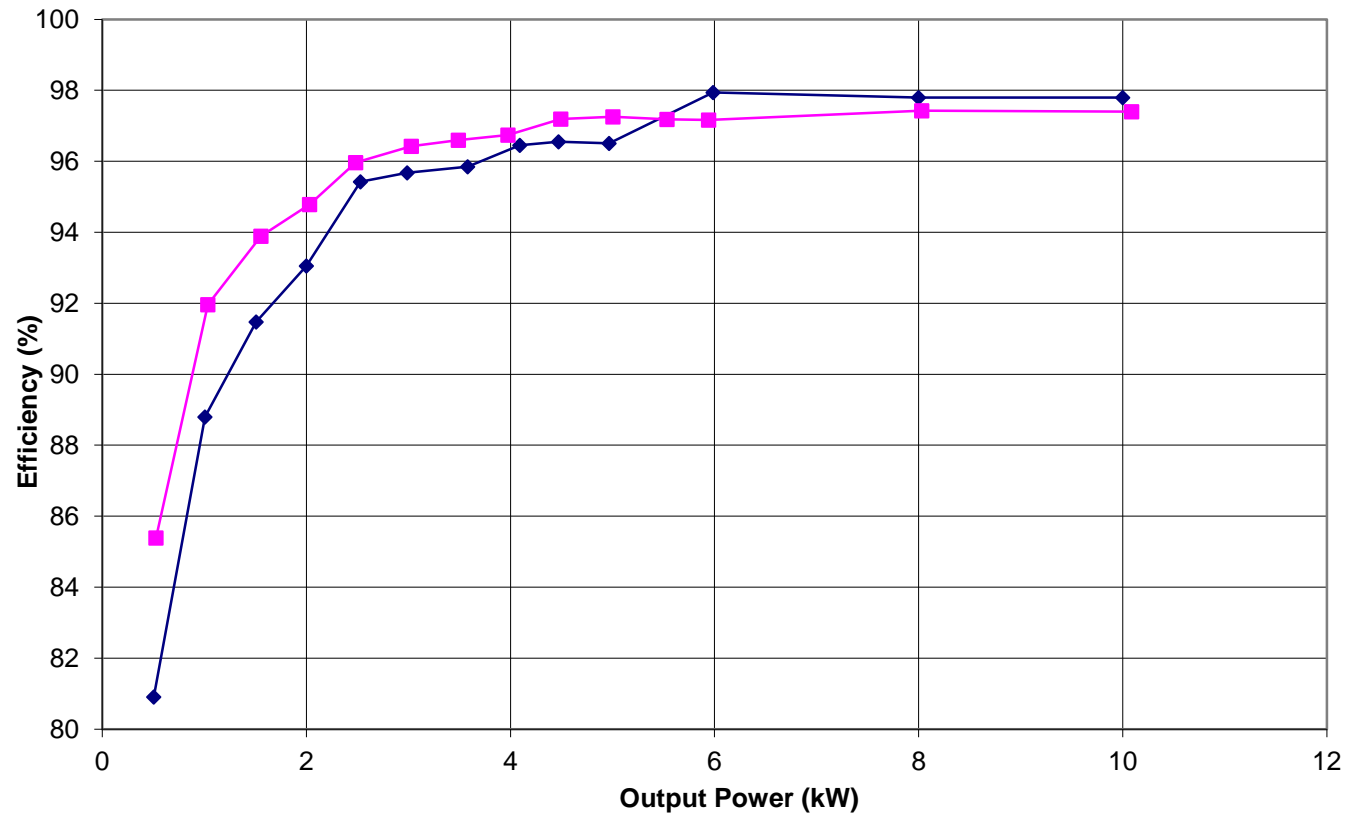
11kW/208VAC 97%-efficiency PFC



Topology

2. Magna 11kW Battery Chargers

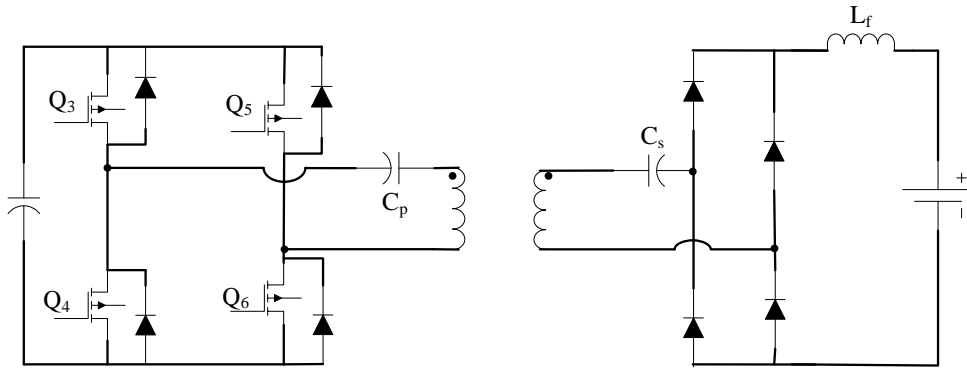
Kettering / Magna PFC Experimental Efficiency Data



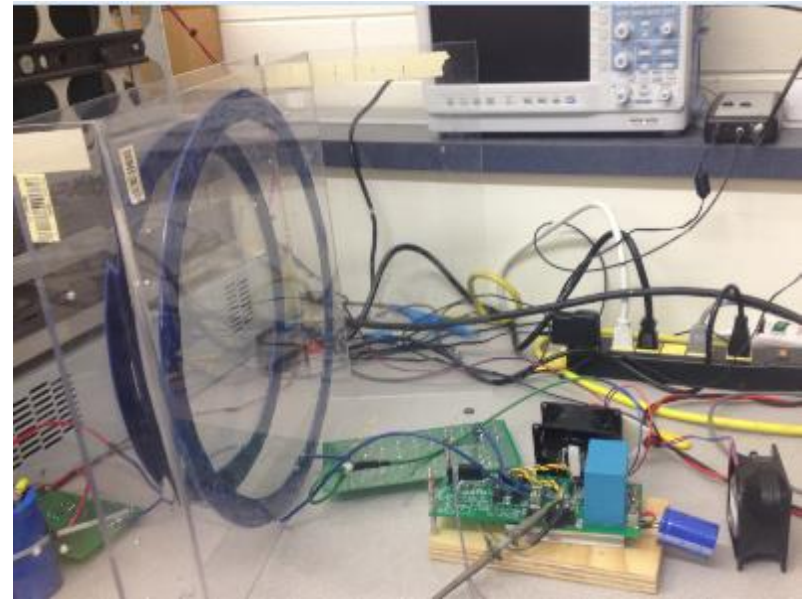
#1. with FRR

#2. With SiC Schottky Diode

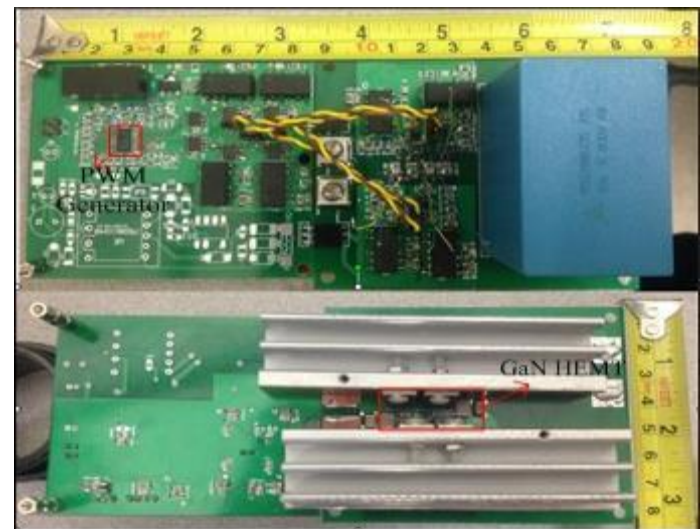
3. GaN Based Wireless Charger



WBG based wireless charger

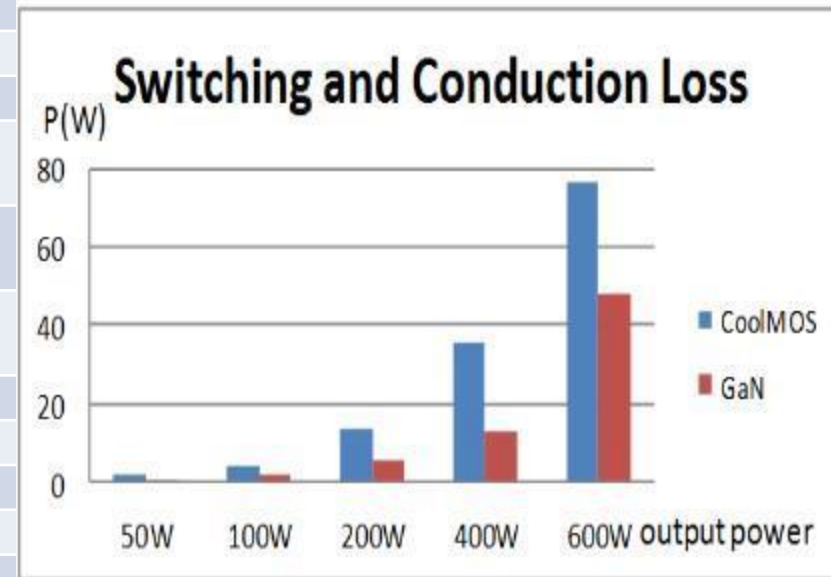


G2 Wireless Charger, D=20cm

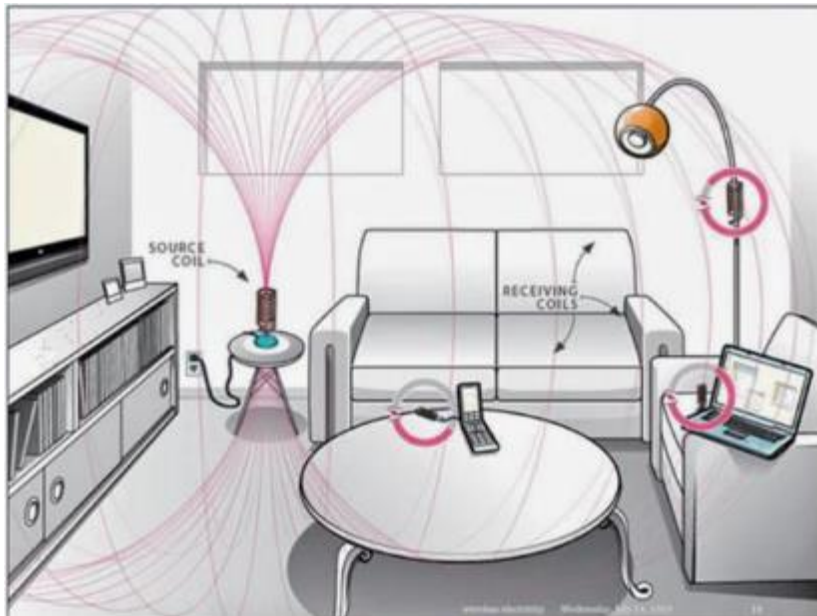


3. GaN Based Wireless Charger

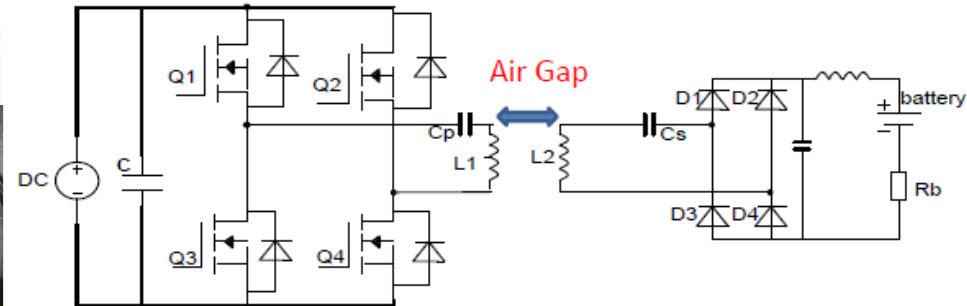
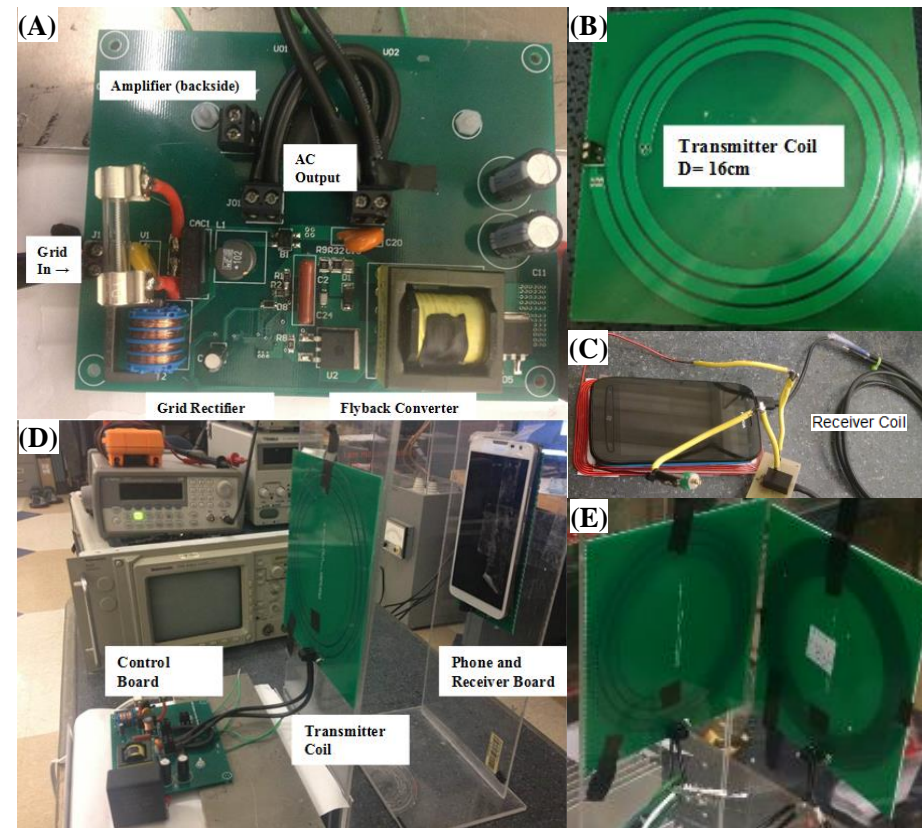
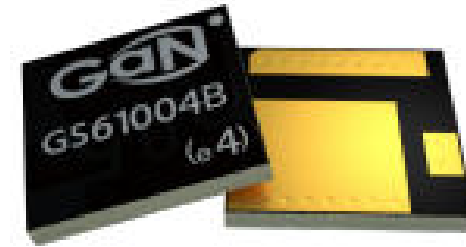
Parameter	Value	Unit
Switching frequency	813	kHz
Dead time	90	ns
PWM duty cycle	43%	
Turn on/off resistance for GaN HEMT	8.2	Ω
Self-inductance of primary side	30.87	μH
Self-inductance of secondary side	25.62	μH
Mutual inductance	5.52	μH
Input voltage	150	V
Input average current	1.34	A
Output voltage	48	V
Output current	3.8	A



4. GaN based Cell-phone Wireless Charger



4. GaN based Cell-phone Wireless Charger



Switching frequency 6MHz;

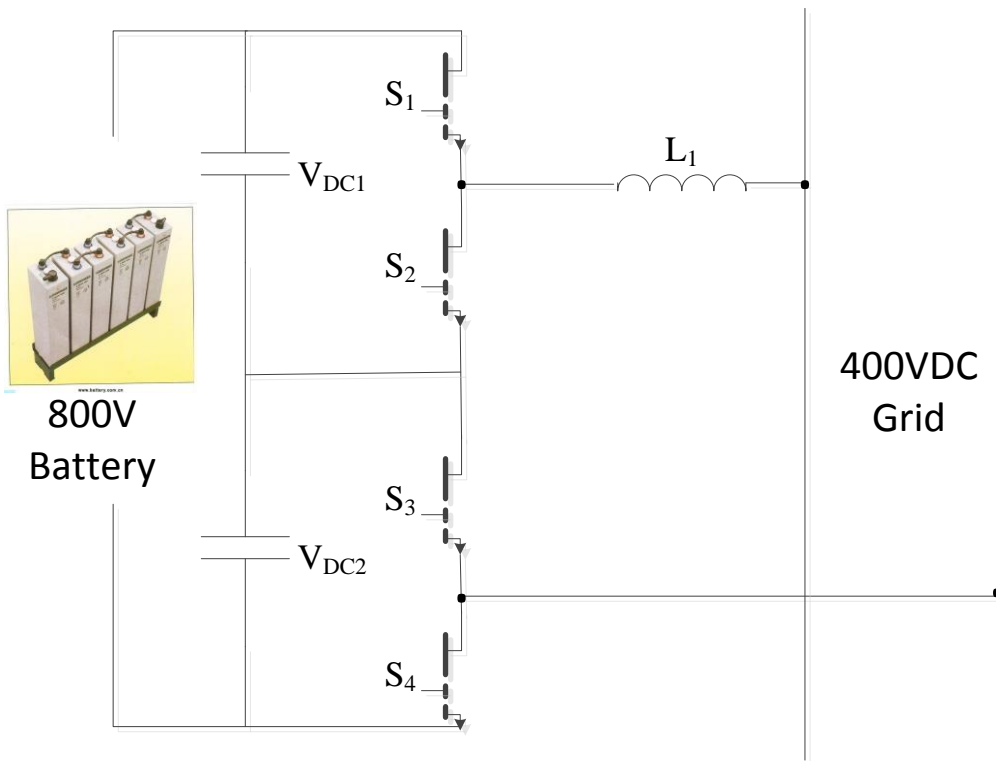
Overall efficiency ~40%;

>10W per phone;

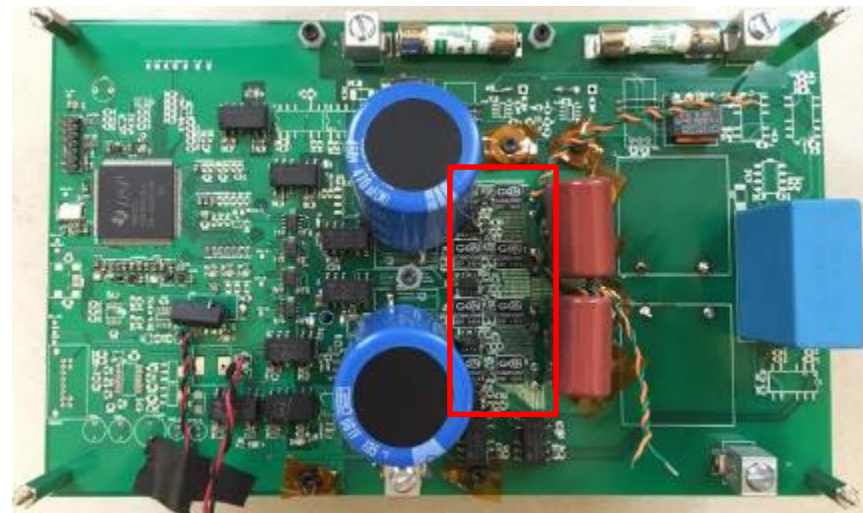
Multiple phone charging

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5. GaN based Smart Grid System

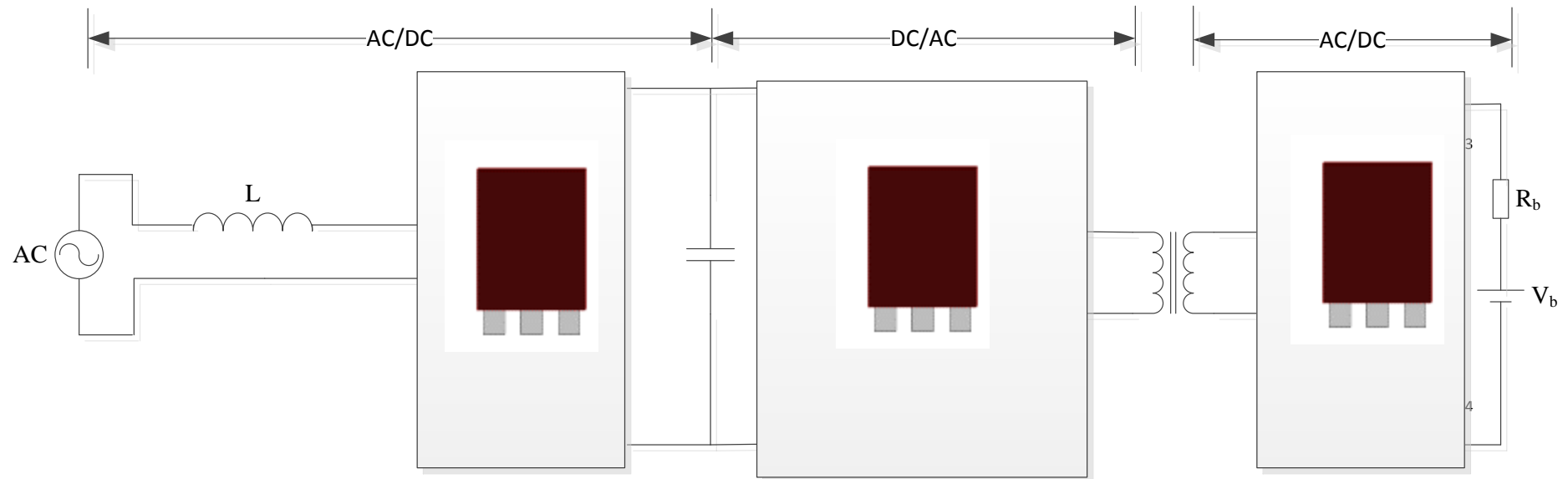


Smart-Grid Infrastructure



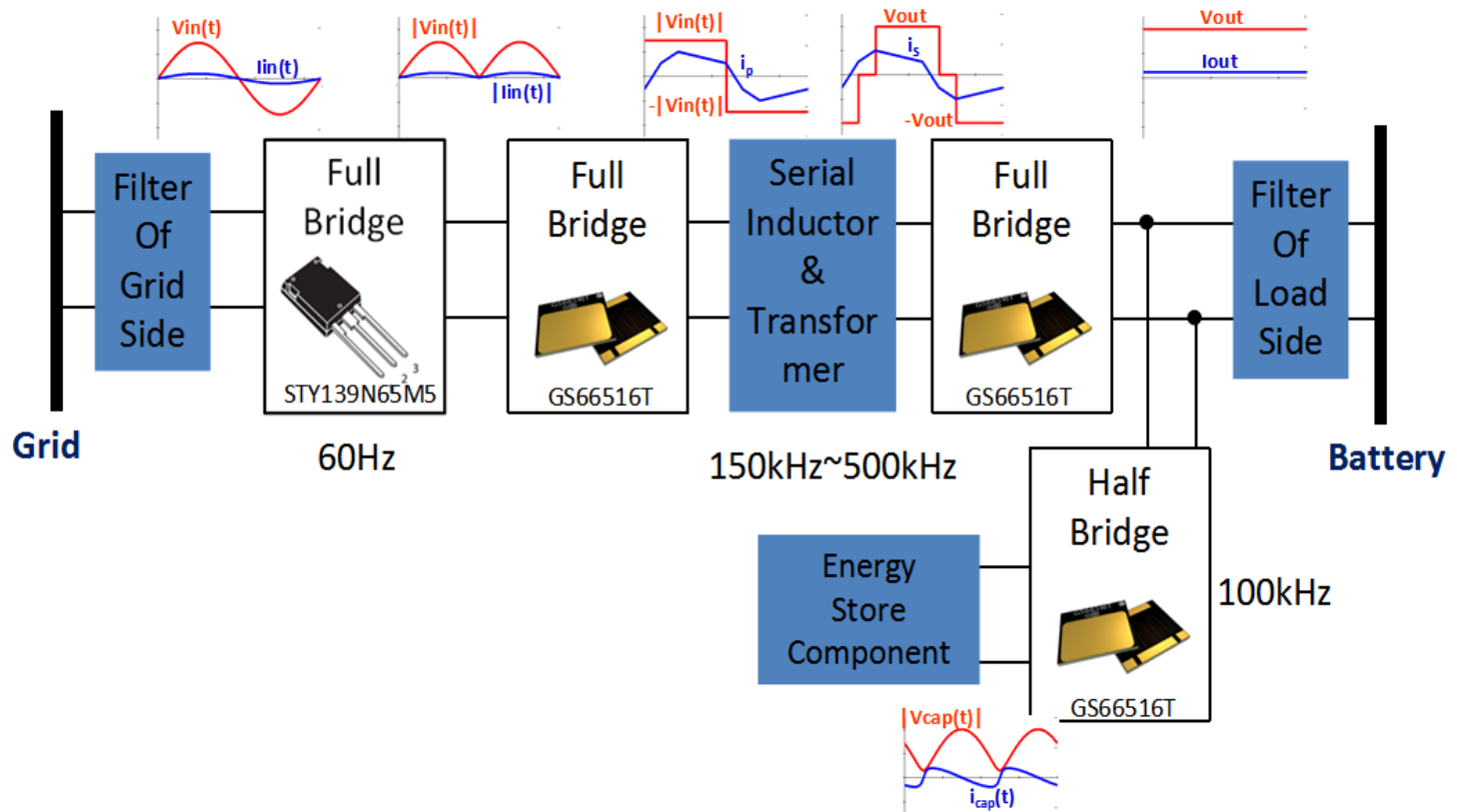
Bidirectional DCDC Converter using GaN

6. GaN based 97%-efficiency Charger



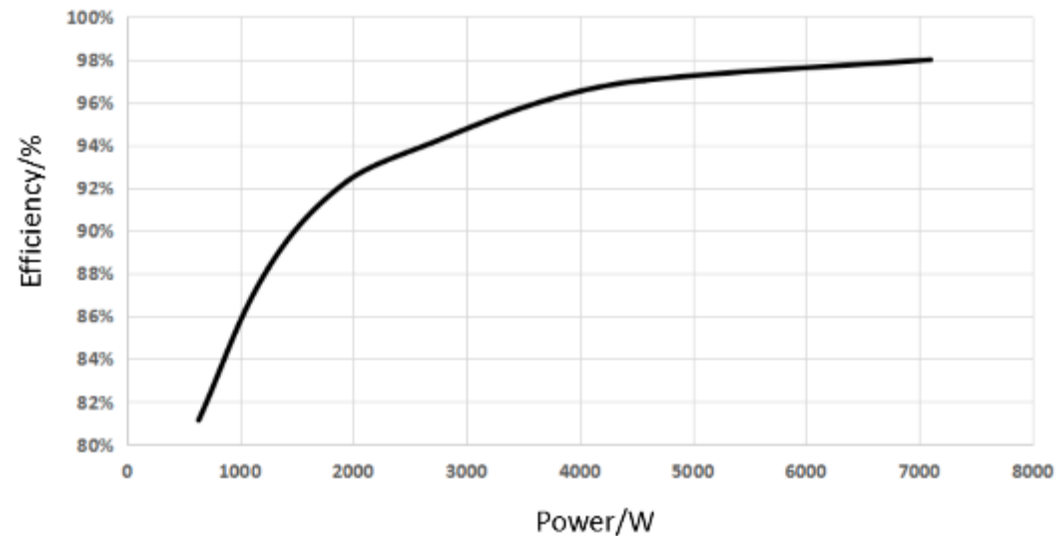
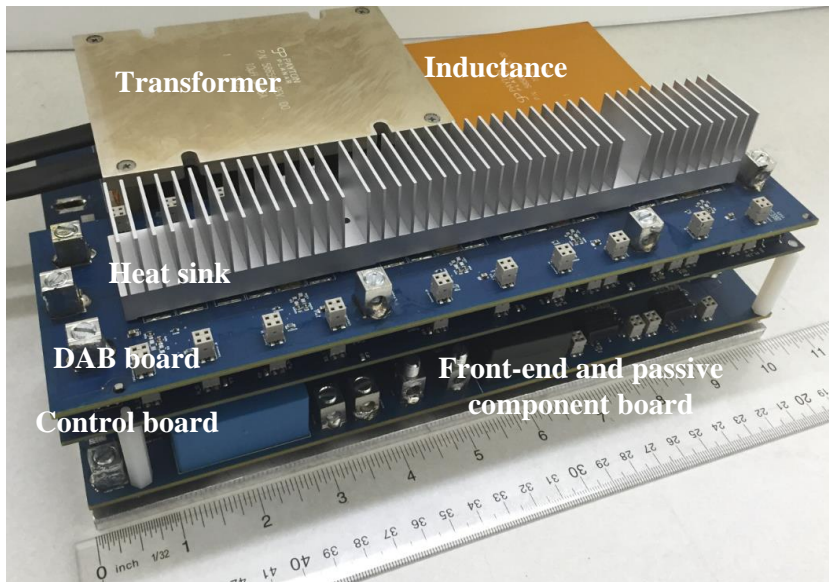
94%-efficiency Conventional Charger

6. GaN based 97%-efficiency Charger



97%-efficiency Charger

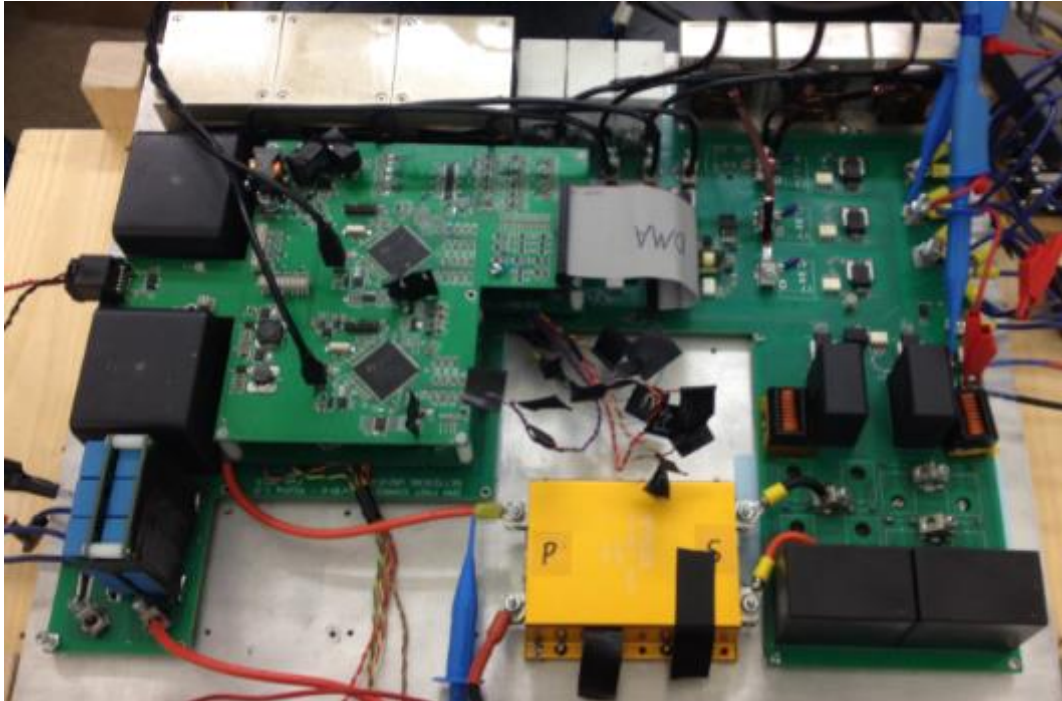
6. GaN based 97%-efficiency Charger



1st version charger (>2.6kW/L)
2nd version charger (>4kW/L)

Efficiency Curves

7. SiC 24kW On-board Charger



- 24kW charging power;
- 96% efficiency at 20kW;
- All SiC devices;
- Hard switching at PFC;
- Soft switching at DCDC;
- >2.4kW/L.

8. SiC 120kW Charging Station



Xuntuo Wang

Xuntuo (Nelson) Wang is currently a 3rd year Ph.D. Candidate and Irwin Mark Jacobs and Joan Klein Jacobs Presidential Fellow in the Department of Electrical Engineering and Computer Science at MIT. He has two years research experience in the EV field. Nelson is honored to serve as President and CTO of CZAR-POWER and is committed to future collaboration with industry and research universities.



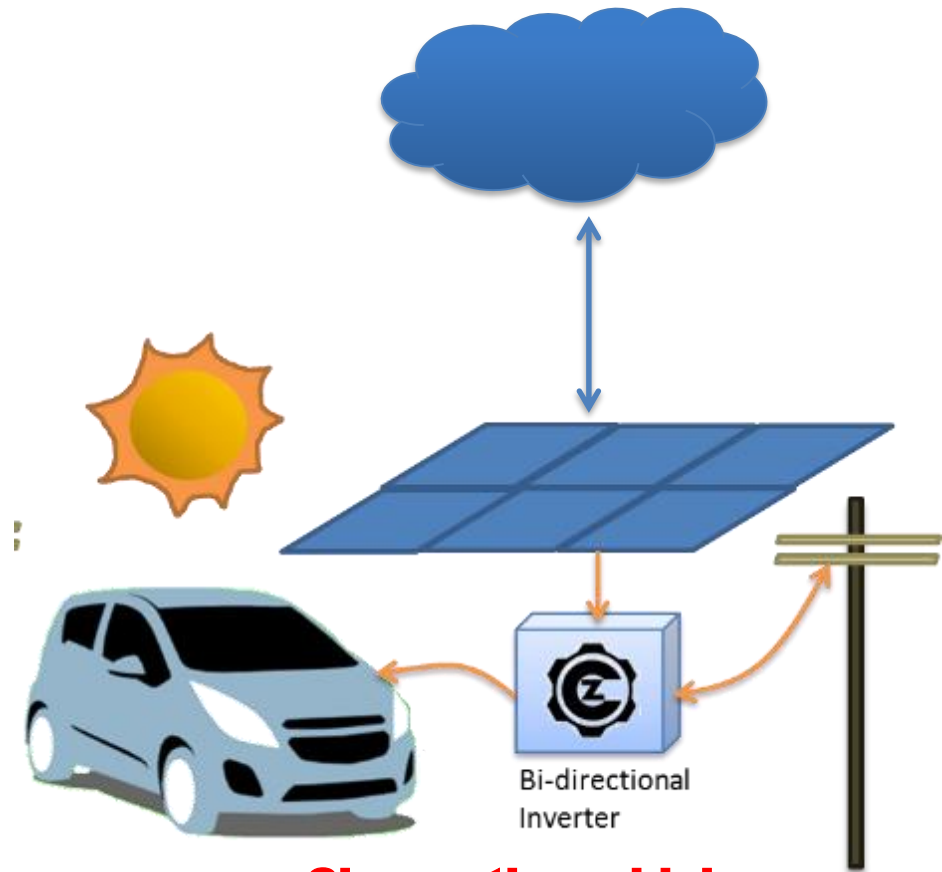
Dr. Hua (Kevin) Bai

Hua (Kevin) Bai received BS and Ph.D. from Department of Electrical Engineering of Tsinghua University, Beijing, China in 2002 and 2007, respectively. He is the author of 1 book (Transients of Modern Power Electronics), 35 peer-reviewed IEEE journal papers, 18 conference papers, and he holds 5 industrial patents.



Dr. James L. Kirtley Jr.

Dr. James L. Kirtley Jr. is of Professor of Electrical Engineering at the Massachusetts Institute of Technology. Dr. Kirtley attended MIT as an undergraduate and received the degree of Ph.D. from MIT in 1971. Dr. Kirtley is a specialist in electric machinery and electric power systems. He served as Editor in Chief of the IEEE Transactions on Energy Conversion from 1998 to 2006 and continues to serve as Editor for that journal and as a member of the Editorial Board of the journal Electric Power Components and Systems. Dr. Kirtley was made a Fellow of IEEE in 1990. He was awarded the IEEE Third Millennium medal in 2000 and the Nikola Tesla prize in 2002. Dr. Kirtley was



Charge the vehicle

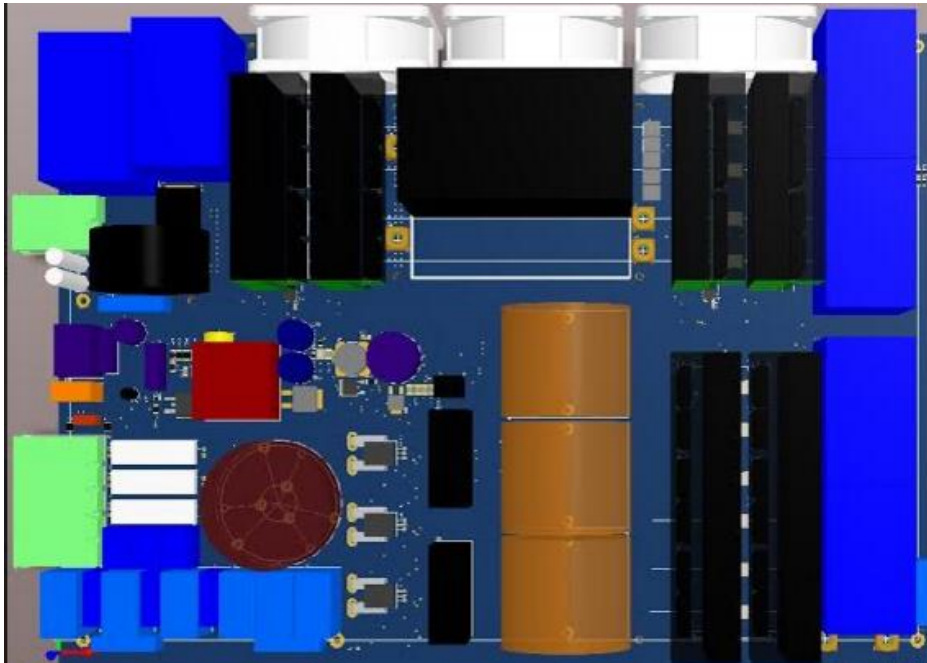
Support the grid

Cloud technology

Renewable energy

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8. SiC 120kW Charging Station



**Final Charger Module
(~3.3kW/L)**

- 24kW bidirectional ;
- 96% efficiency at 20kW;
- All SiC devices;
- Hard switching at PFC;
- Soft switching at DCDC;
- >3.3kW/L;
- Incorporating solar energy

Summary

- 1) Higher efficiency and high power density are always the pursuit of power electronics engineers and scholars;**
- 2) Wide-bandgap devices are the present hot point and might replace present Si devices once the cost drops;**
- 3) Wide-bandgap devices will push Silicon device to enhance its performance continuously;**
- 4) Simply replacing Silicon devices with wide-bandgap devices on the presently existing systems won't work.**

Acknowledgement



Thank you!

Questions?